L Number	Hits	Search Text	DB	Time stamp
1	434	CHEN-COMING-.in. WU-JUAN-YUAN-.in. WU-J-Y-.in. LUR-WATER-.in. LUR-W-.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:20
2	11	(("20020031726") or ("20020001919") or ("20030056191") or ("20020025689") or ("20010001191") or ("20020146914")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:18
3	9294	sti! (shallow adj trench adj isolation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:21
4	35565	active adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:21
5	106219	silicon adj nitride "si.sub.3 n.sub.4" si3n4 sixny "si.sub.x n.sub.y"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:22
6	337	(active adj region) near2 small	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:22
7	276	(active adj region) near2 large	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:22
8	64948	trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:22
9	1147369	oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:22
11	957	hpcvd hdpcvd hdp-cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:28
12	1788	((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit$5) cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:30
13	36072	planariz$5 planaris$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:30
14	32913	cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:31
15	4	(("6291111") or ("6178543")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:33

10	16	partial adj reverse adj2 (mask active photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:41
16	217	((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit$5) cvd))) with oxide with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:38
17	161	(sti! (shallow adj trench adj isolation)) and ((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit$5) cvd))) with oxide with trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:38
18	139	(sti! (shallow adj trench adj isolation)) and ((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit$5) cvd))) with oxide with trench) and (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:38
19	114	(sti! (shallow adj trench adj isolation)) and ((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit$5) cvd))) with oxide with trench) and (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) and (silicon adj nitride "si.sub.3 n.sub.4" si3n4 sixny "si.sub.x n.sub.y")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:38
20	100	(sti! (shallow adj trench adj isolation)) and ((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit$5) cvd))) with oxide with trench) and (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) and (silicon adj nitride "si.sub.3 n.sub.4" si3n4 sixny "si.sub.x n.sub.y") and (resist photoresist mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:40
21	7	(sti! (shallow adj trench adj isolation)) and ((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit$5) cvd))) with oxide with trench) and (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) and (silicon adj nitride "si.sub.3 n.sub.4" si3n4 sixny "si.sub.x n.sub.y") and (resist photoresist mask) and ((active adj region) near2 small) and ((active adj region) near2 large)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:41

23	93	((sti! (shallow adj trench adj isolation)) and (((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit$5) cvd))) with oxide with trench) and (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) and (silicon adj nitride "si.sub.3 n.sub.4" si3n4 sixny "si.sub.x n.sub.y") and (resist photoresist mask)) not (((sti! (shallow adj trench adj isolation)) and (((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit$5) cvd))) with oxide with trench) and (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) and (silicon adj nitride "si.sub.3 n.sub.4" si3n4 sixny "si.sub.x n.sub.y") and (resist photoresist mask) and ((active adj region) near2 small) and ((active adj region) near2 large)) (partial adj reverse adj2 (mask active photoresist)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:07
25	4	(("6291111") or ("6178543")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:55
27	396	oxide with (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) with (remov$3 strip$4) with etch$5	USPAT	2003/03/27 15:33
28	42	oxide with (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) with (remov$3 strip$4) with etch$5 with (known conventional$3 typical$3)	USPAT	2003/03/27 15:45
29	66	oxide with (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) with (planariz$5 planaris$5) with etch$5 with (known conventional$3 typical$3)	USPAT	2003/03/27 15:50
30	20	(oxide with (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) with (planariz$5 planaris$5) with etch$5 with (known conventional$3 typical$3)) and (sti! (shallow adj trench adj isolation))	USPAT	2003/03/27 15:54
31	46	(oxide with (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) with (planariz$5 planaris$5) with etch$5 with (known conventional$3 typical$3)) not ((oxide with (cmp (((chemical$3 adj mechanical$3) (chemical$3-mechanical$3)) adj polish$3) chemical$3-mechanical$3-polish$3) with (planariz$5 planaris$5) with etch$5 with (known conventional$3 typical$3)) and (sti! (shallow adj trench adj isolation)))	USPAT	2003/03/27 15:54